

IN THE SPECIFICATION

Please replace the paragraph beginning at page 5, line 11, with the following rewritten paragraph:

The method includes: using the mask with the repeated pattern, for example, having a pattern width of $2\text{ }\mu\text{m}$ and pitch of $0.3\text{ }\mu\text{m}$ formed thereon to form, for example, a polycrystal having a length of $2\text{ }\mu\text{m}$ and width of $0.3\text{ }\mu\text{m}$.